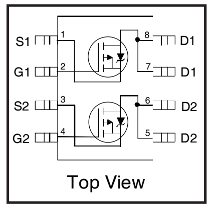
International
IOR Rectifier

AUTOMOTIVE GRADE

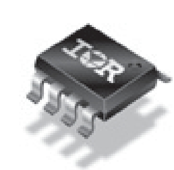
AUIRF7342Q

HEXFET® Power MOSFET

- Advanced Planar Technology
- Low On-Resistance
- Logic Level Gate Drive
- Dual P-Channel MOSFET
- Dynamic dV/dT Rating
- 150°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free, RoHS Compliant
- Automotive Qualified*



$V_{(BR)DSS}$	-55V
$R_{DS(on)}$ max.	0.105Ω
I_D	-3.4A



SO-8
AUIRF7342Q

Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRF7342Q	SO-8	Tube	95	AUIRF7342Q
		Tape and Reel	2500	AUIRF7342QTR

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	-55	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ -10V	-3.4	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ -10V	-2.7	
I_{DM}	Pulsed Drain Current ①	-27	
P_D @T_A = 25°C	Power Dissipation	2.0	W
P_D @T_A = 70°C	Power Dissipation③	1.3	
	Linear Derating Factor	0.016	mW/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
V_{GSM}	Gate-to-Source Voltage Single Pulse tp<10µs	30	V
E_{AS}	Single Pulse Avalanche Energy②	114	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ⑤	62.5	°C/W

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*Qualification standards can be found at http://www.irf.com/

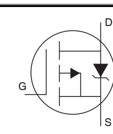
Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-55	——	——	V	V_{GS} = 0V, I_D = -250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	-0.054	——	V/°C	Reference to 25°C, I_D = -1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	0.095	0.105	Ω	V_{GS} = -10V, I_D = -3.4A ④
		——	0.150	0.170		V_{GS} = -4.5V, I_D = -2.7A ④
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	——	-3.0	V	V_{DS} = V_{GS}, I_D = -250μA
gfs	Forward Transconductance	3.3	——	——	S	V_{DS} = -10V, I_D = -3.1A
I_{DSS}	Drain-to-Source Leakage Current	——	——	-2.0	μA	V_{DS} = -55V, V_{GS} = 0V
		——	——	-25		V_{DS} = -55V, V_{GS} = 0V, T_J = 55°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	-100	nA	V_{GS} = -20V
	Gate-to-Source Reverse Leakage	——	——	100		V_{GS} = 20V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	——	26	38	nC	I_D = -3.1A
Q_{gs}	Gate-to-Source Charge	——	3.0	4.5		V_{DS} = -44V
Q_{gd}	Gate-to-Drain ("Miller") Charge	——	8.4	13		V_{GS} = -10V, See Fig. 10 ④
$t_{d(on)}$	Turn-On Delay Time	——	14	22	ns	V_{DD} = -28V
t_r	Rise Time	——	10	15		I_D = -1.0A
$t_{d(off)}$	Turn-Off Delay Time	——	43	64		R_G = 6.0Ω
t_f	Fall Time	——	22	32		R_D = 16Ω ④
C_{iss}	Input Capacitance	——	690	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	210	——		V_{DS} = -25V
C_{rss}	Reverse Transfer Capacitance	——	86	——		ƒ = 1.0MHz, See Fig. 9

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	-2.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	-27		
V_{SD}	Diode Forward Voltage	——	——	-1.2	V	T_J = 25°C, I_S = -2.0A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	——	54	80	ns	T_J = 25°C, I_F = -2.0A
Q_{rr}	Reverse Recovery Charge	——	85	130	nC	di/dt = 100A/μs ③

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 20mH, R_G = 25Ω, I_{AS} = -3.4A. (See Figure 8)

③ I_{SD} ≤ -3.4A, di/dt ≤ -150A/μs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150°C.

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

⑤ When mounted on 1 inch square copper board, t<10 sec.

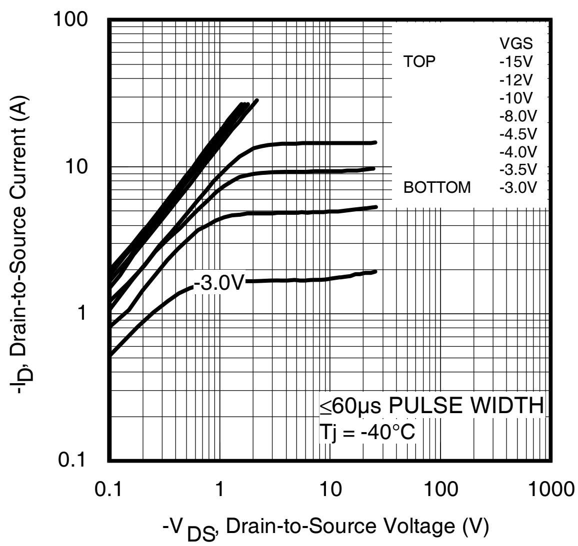


Fig 1. Typical Output Characteristics

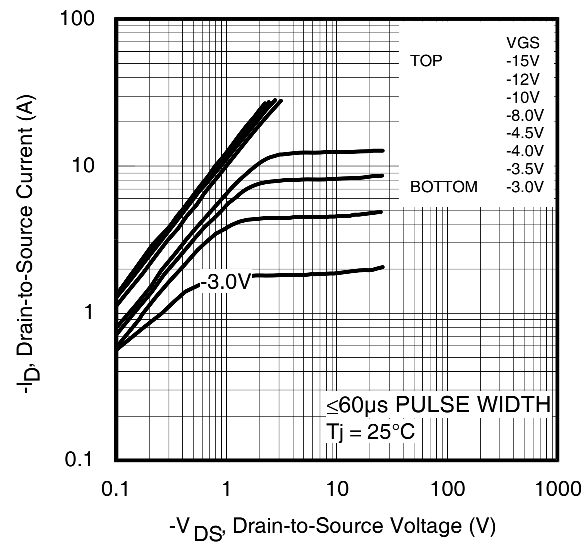


Fig 2. Typical Output Characteristics

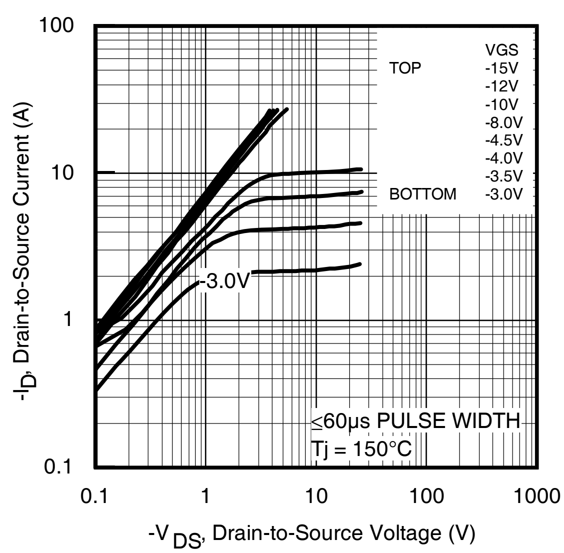


Fig 3. Typical Output Characteristics

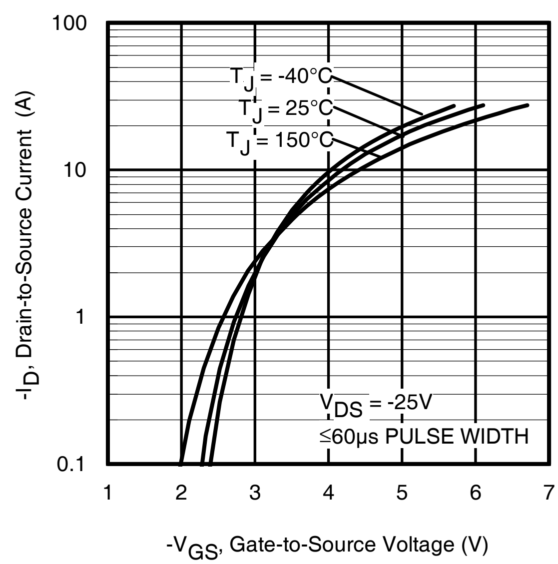


Fig 4. Typical Transfer Characteristics

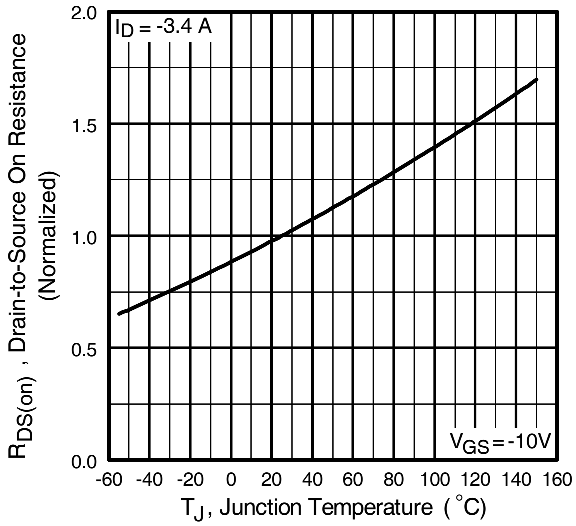


Fig 5. Normalized On-Resistance vs. Temperature

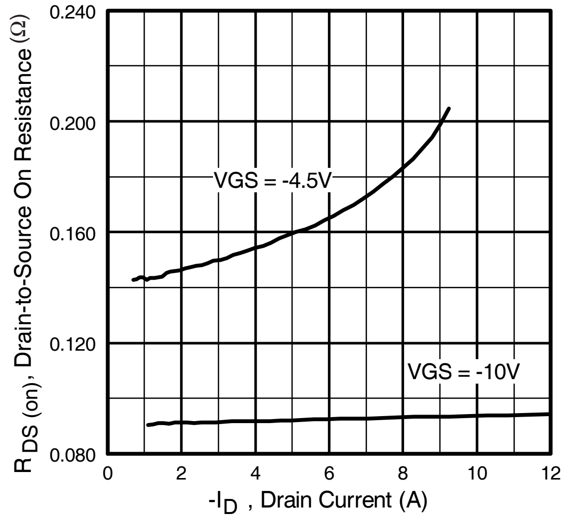


Fig 6. Typical On-Resistance Vs. Drain Current

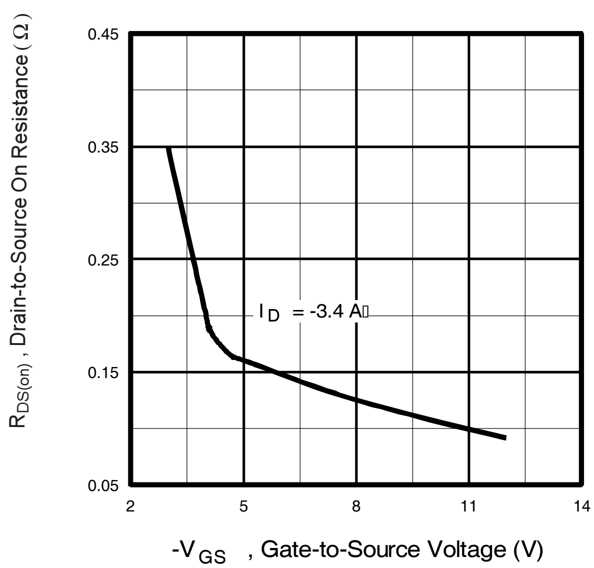


Fig 7. Typical On-Resistance vs. Gate Voltage

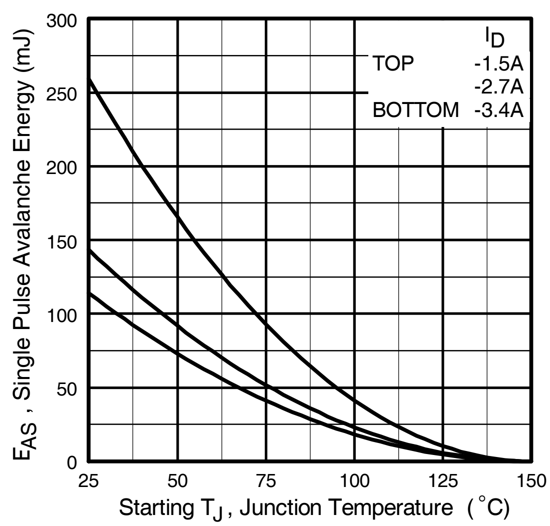


Fig 8. Maximum Avalanche Energy vs. Drain Current

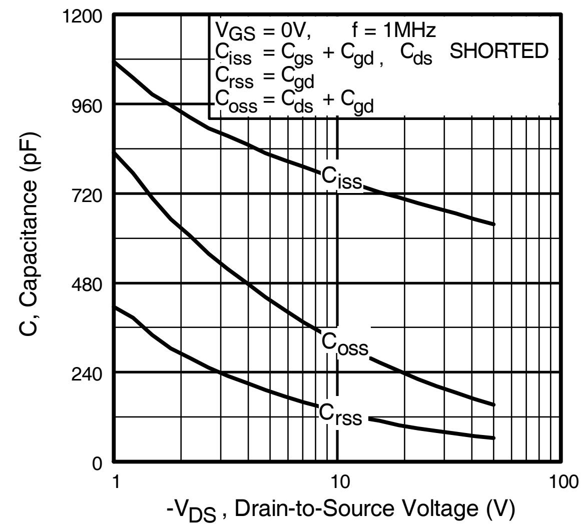


Fig 9. Typical Capacitance vs. Drain-to-Source Voltage

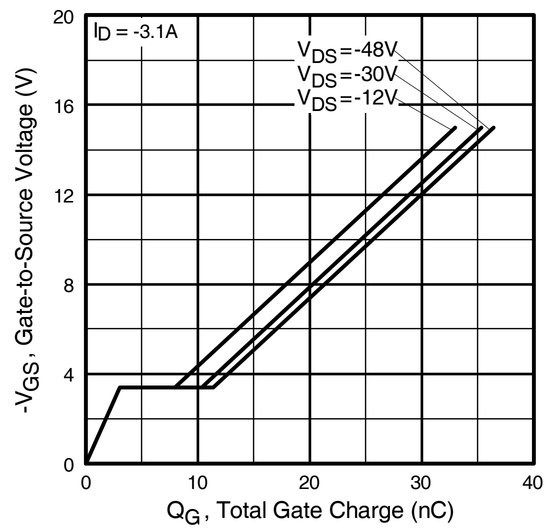


Fig 10. Typical Gate Charge vs. Gate-to-Source Voltage

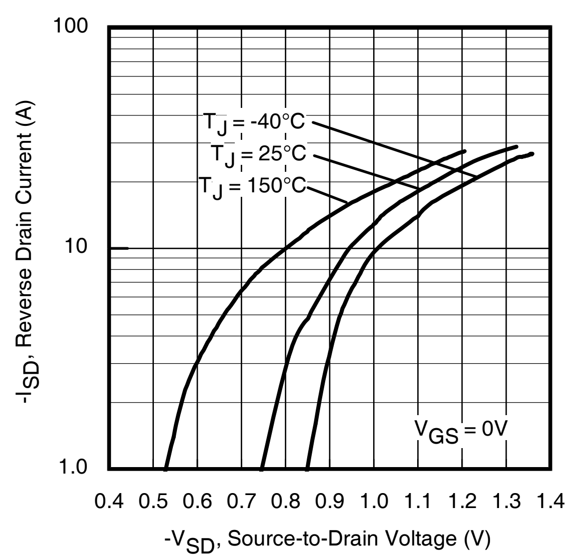


Fig 11. Typical Source-Drain Diode Forward Voltage

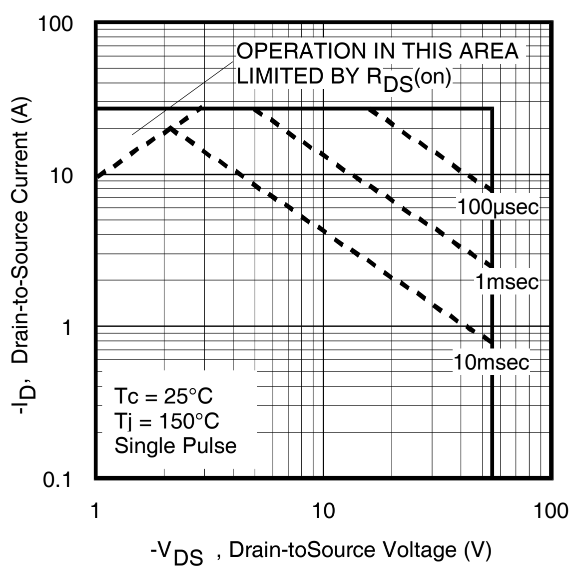


Fig 12. Maximum Safe Operating Area

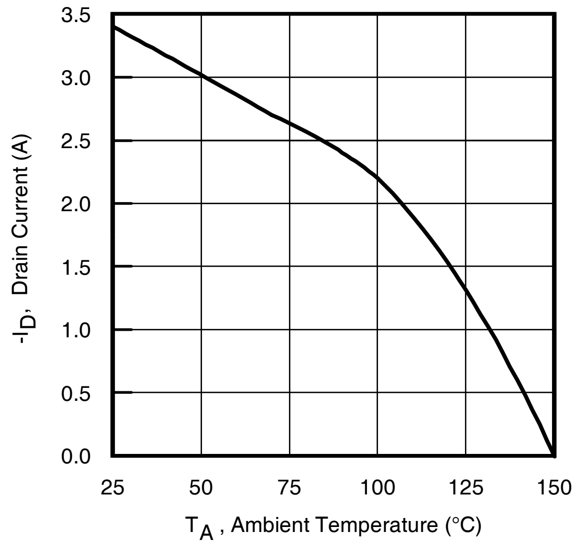


Fig 13. Maximum Drain Current vs. Ambient Temperature

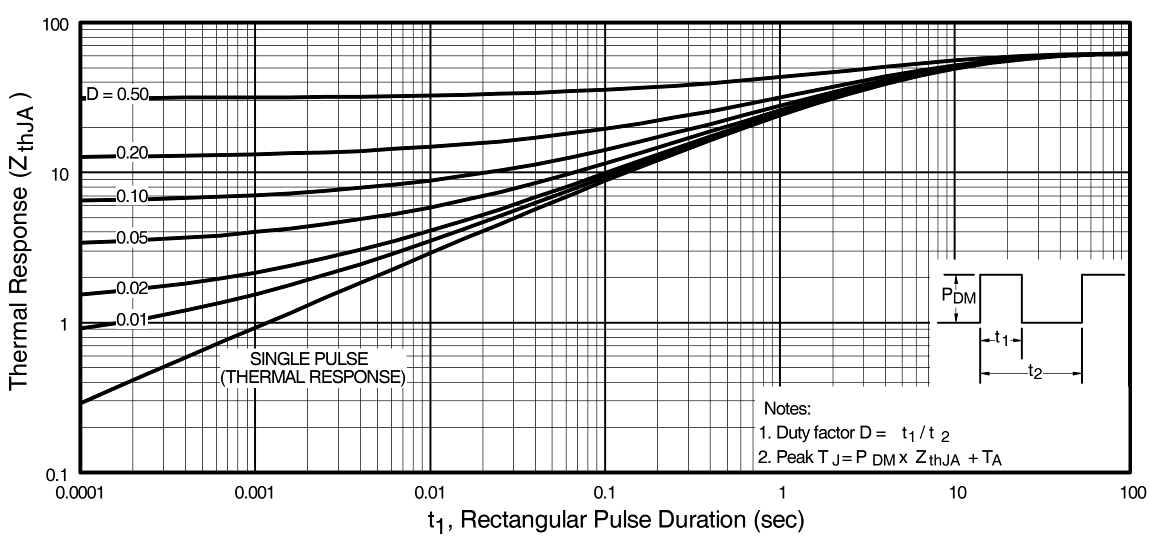
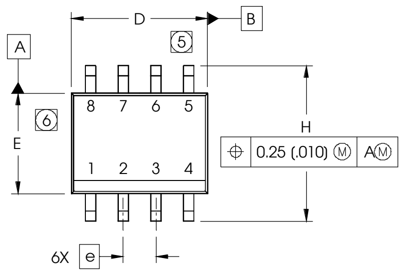


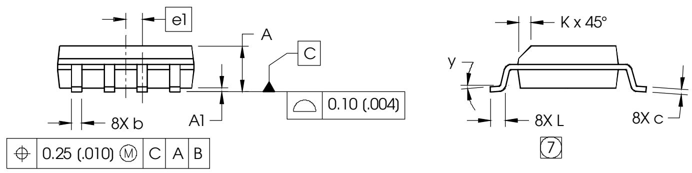
Fig 14. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

SO-8 Package Outline

Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



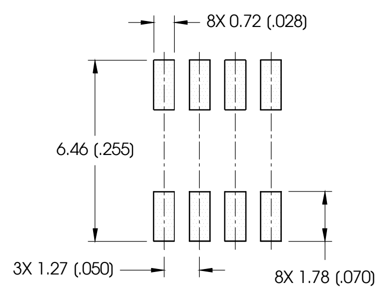
NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.

5 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].

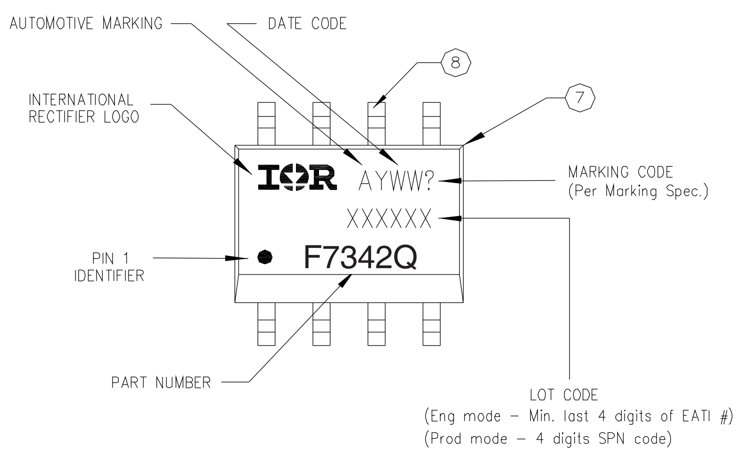
6 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].

7 DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



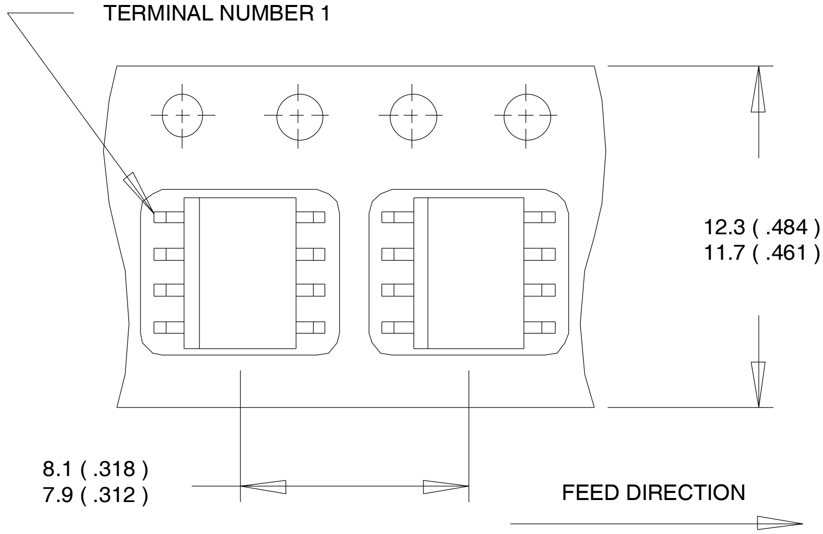
SO-8 Part Marking



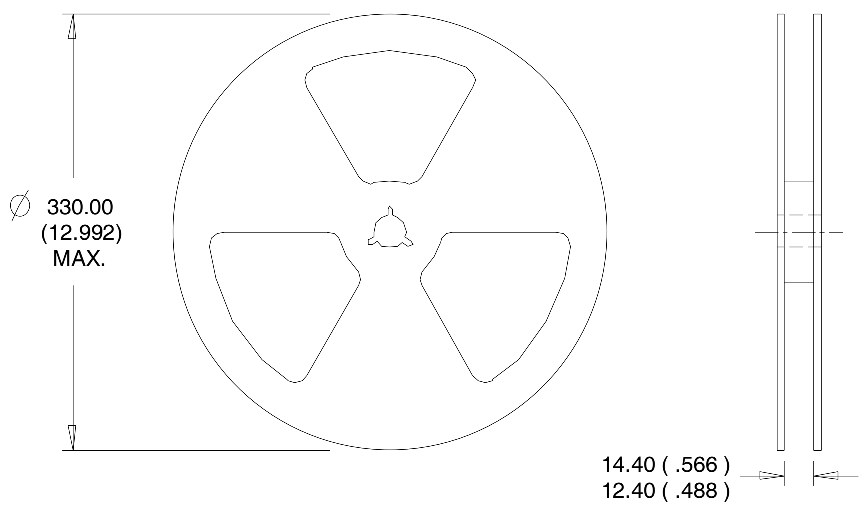
Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) [††]	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		SO-8	MSL1
ESD	Machine Model	Class M2 (+/- 200V)[†††] AEC-Q101-002	
	Human Body Model	Class H1A (+/- 500V)[†††] AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 1125V)[†††] AEC-Q101-005	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: http//www.irf.com/

†† Exceptions to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage.

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http://www.irf.com/technical-info/

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Revision History

Date	Comments
3/27/2014	• Added "Logic Level Gate Drive" bullet in the features section on page 1 • Updated data sheet with new IR corporate template